

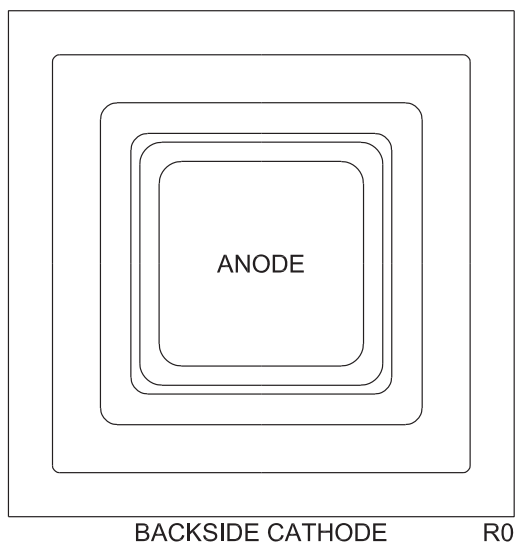
PROCESS CPD89V
Switching Diode
High Current Diode Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	12.8 x 12.8 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	5.1 x 5.1 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 10,000Å

GEOMETRY



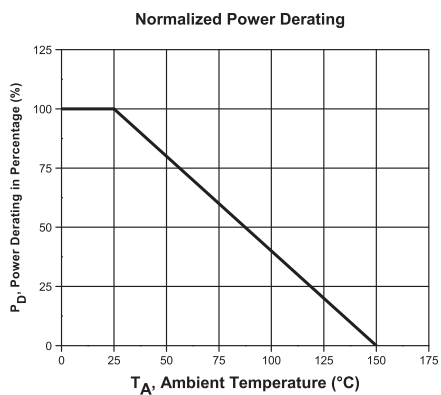
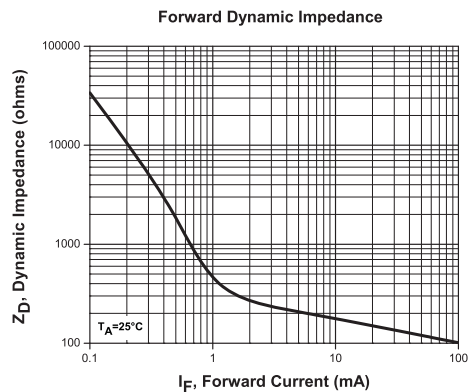
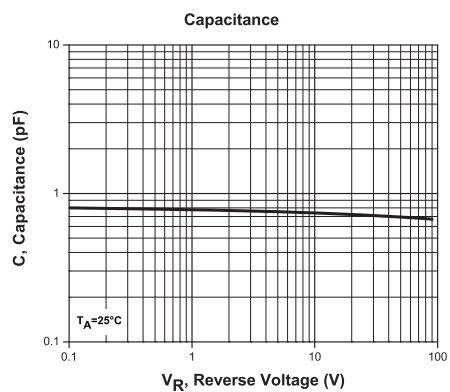
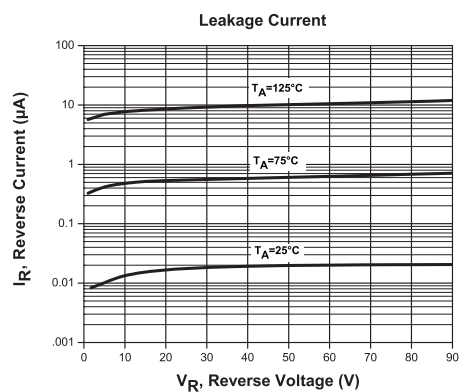
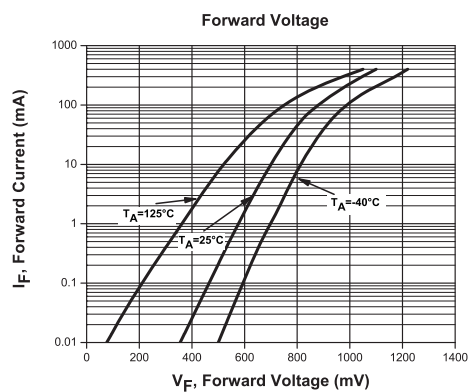
GROSS DIE PER 5 INCH WAFER
103,344

PRINCIPAL DEVICE TYPES
CMPD1001 SERIES
CMPD5001 SERIES

R1 (22-March 2010)

PROCESS CPD89V

Typical Electrical Characteristics



R1 (22-March 2010)